

2SJ506(L), 2SJ506(S)

Silicon P Channel MOS FET
High Speed Power Switching

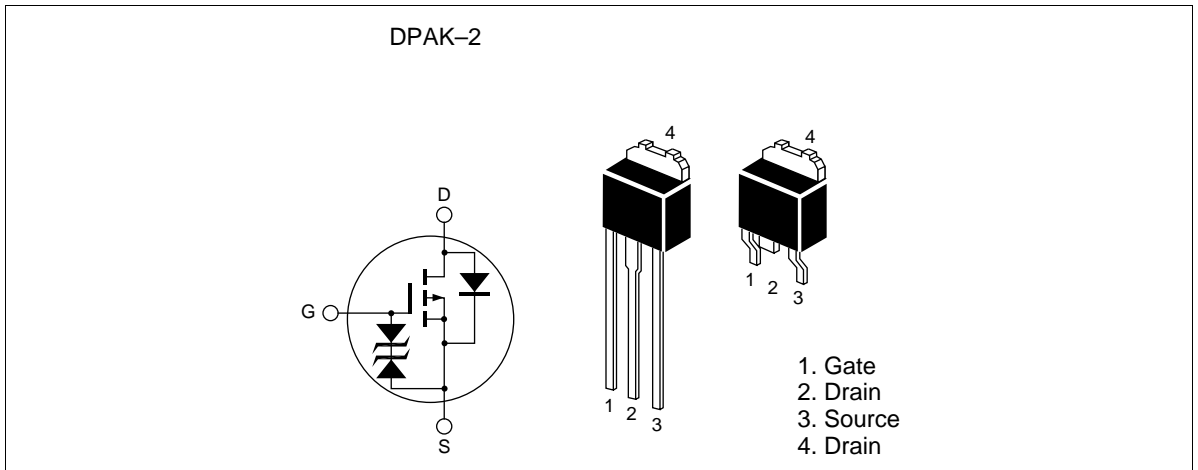
HITACHI

ADE-208-548
Target Specification 1st. Edition

Features

- Low on-resistance
 $R_{DS(on)} = 0.065 \Omega$ typ. (at $V_{GS} = -10V$, $I_D = -5A$)
- Low drive current
- High speed switching
- 4V gate drive devices.

Outline



2SJ506(L), 2SJ506(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	-30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	-10	A
Drain peak current	I _{D(pulse)} ^{Note1}	-40	A
Body to drain diode reverse drain current	I _{DR}	-10	A
Channel dissipation	Pch ^{Note2}	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10μs, duty cycle ≤ 1 %

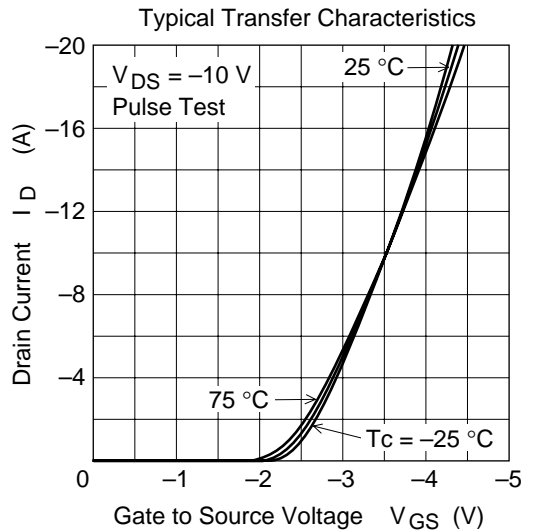
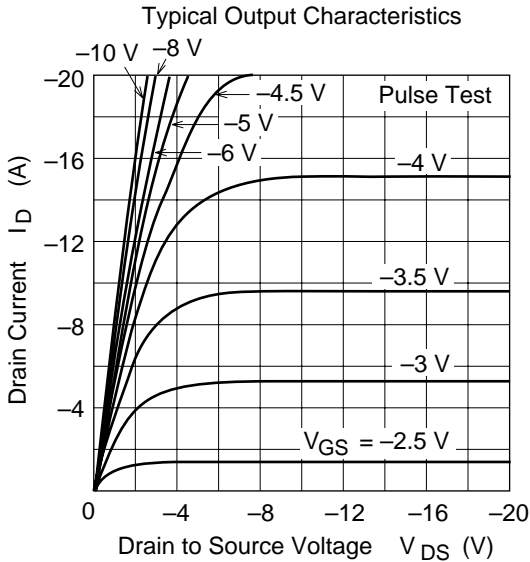
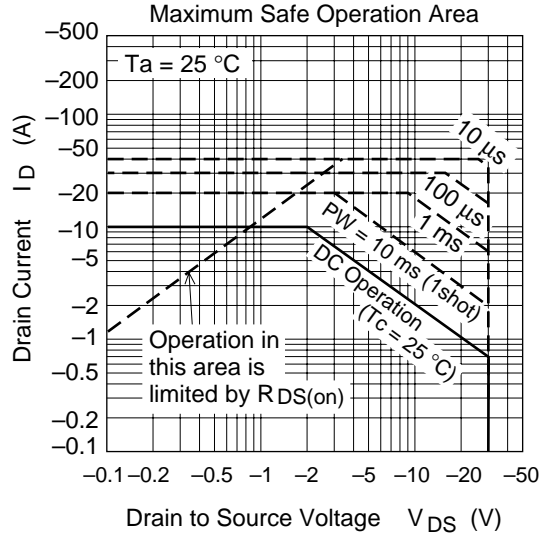
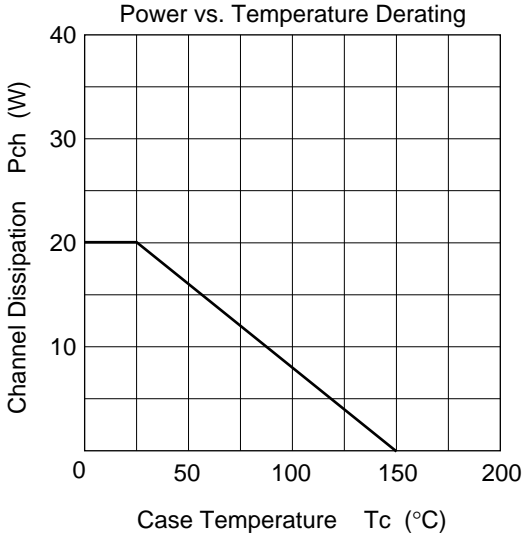
2. Value at Tc = 25°C

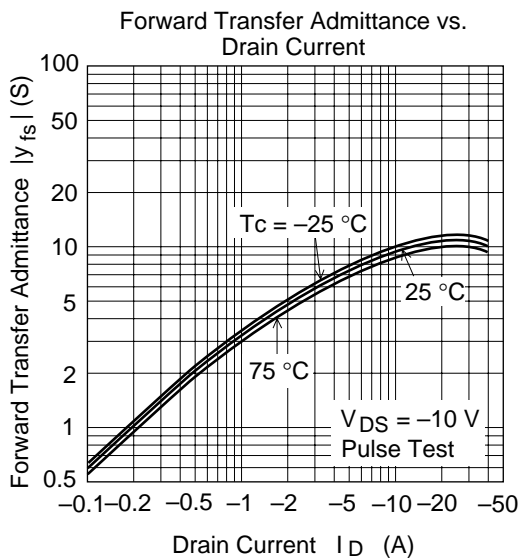
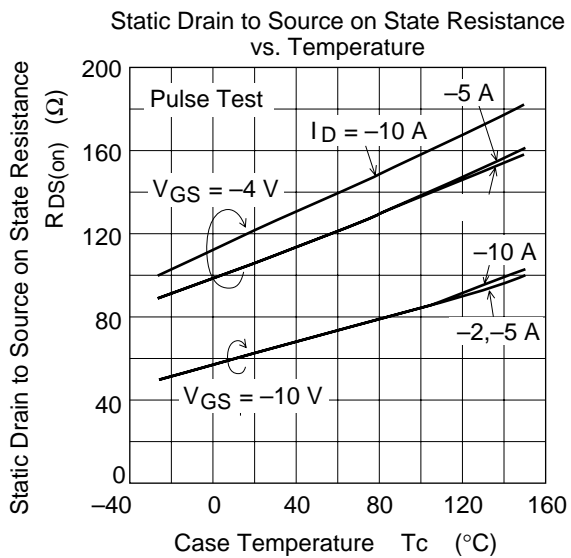
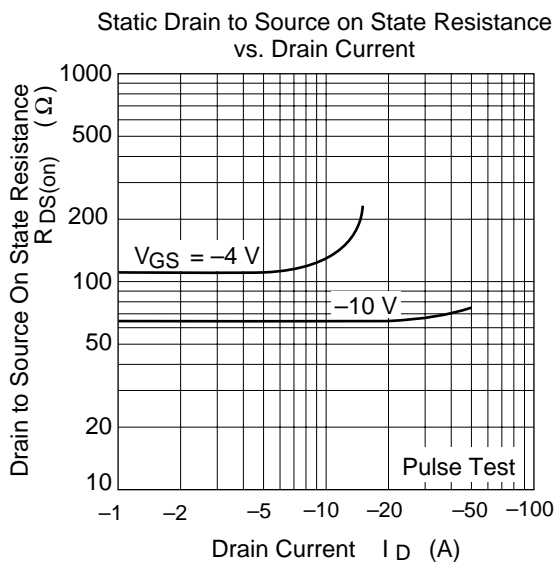
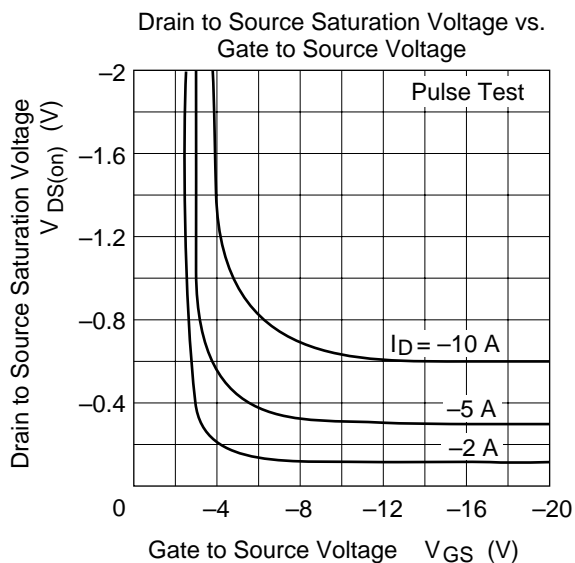
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10\text{mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\mu\text{A}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	μA	$V_{DS} = -30\text{V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16\text{V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1\text{mA}$, $V_{DS} = -10\text{V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	65	85	mΩ	$I_D = -5\text{A}$, $V_{GS} = -10\text{V}$ ^{Note3}
	$R_{DS(on)}$	—	110	180	mΩ	$I_D = -5\text{A}$, $V_{GS} = -4\text{V}$ ^{Note3}
Forward transfer admittance	$ y_{fs} $	10	16	—	S	$I_D = -5\text{A}$, $V_{DS} = -10\text{V}$ ^{Note3}
Input capacitance	C_{iss}	—	660	—	pF	$V_{DS} = -10\text{V}$
Output capacitance	C_{oss}	—	440	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	140	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$I_D = -5\text{A}$, $R_L = 2\Omega$
Rise time	t_r	—	65	—	ns	$V_{GS} = -10\text{V}$
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	
Fall time	t_f	—	65	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.05	—	V	$I_F = -10\text{A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	65	—	ns	$I_F = -10\text{A}$, $V_{GS} = 0$ $diF/dt = 50\text{A}/\mu\text{s}$

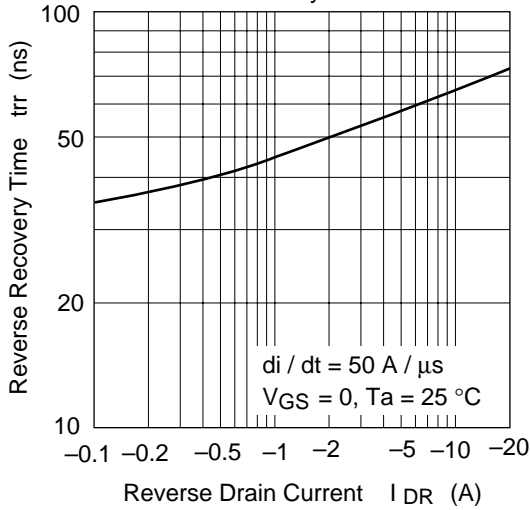
Note: 3. Pulse test

Main Characteristics

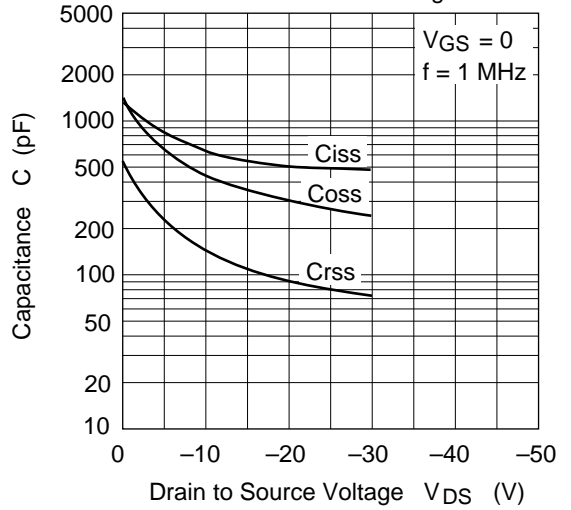




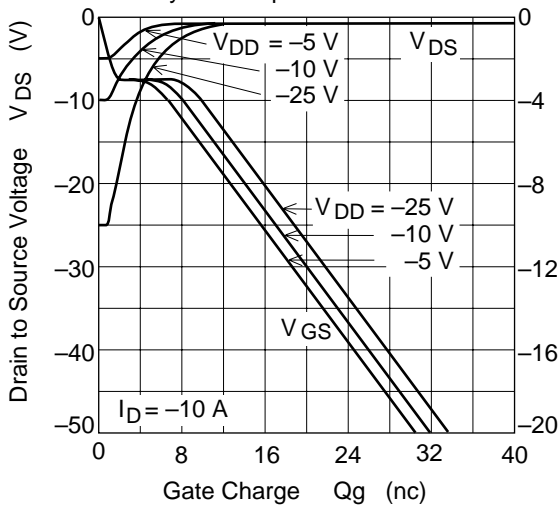
Body to Drain Diode Reverse Recovery Time



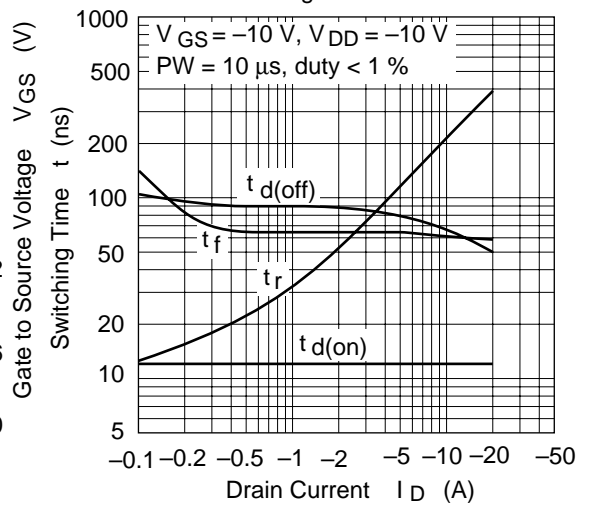
Typical Capacitance vs. Drain to Source Voltage

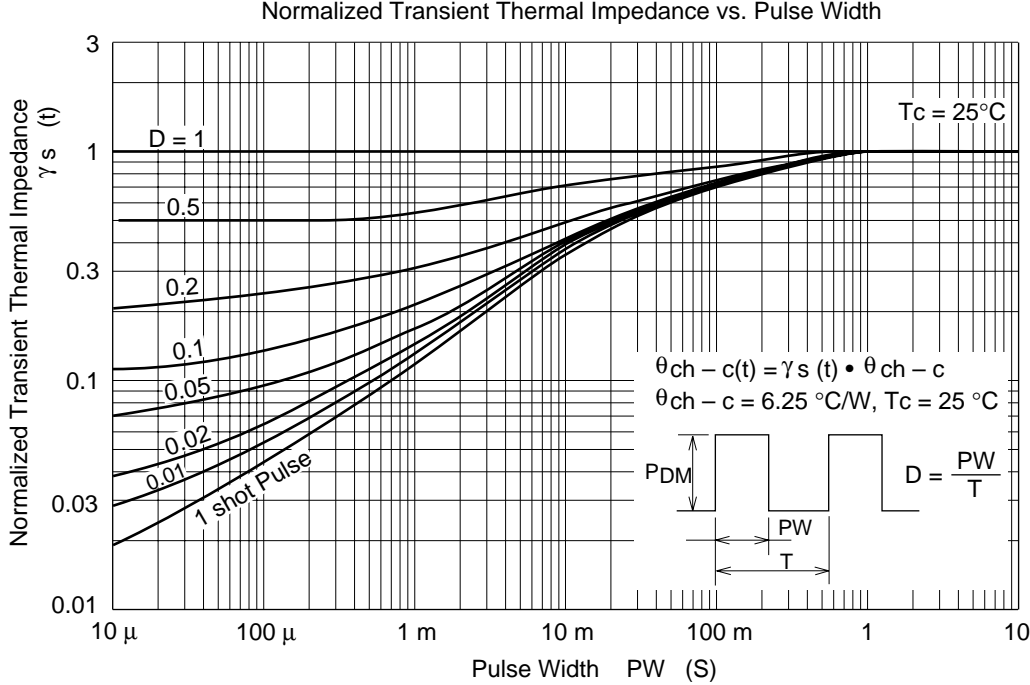
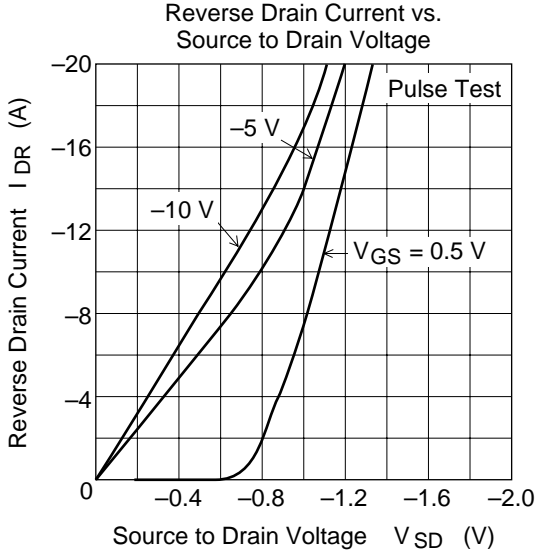


Dynamic Input Characteristics



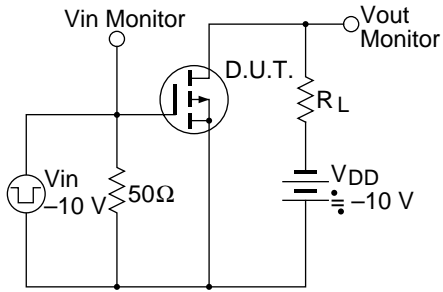
Switching Characteristics



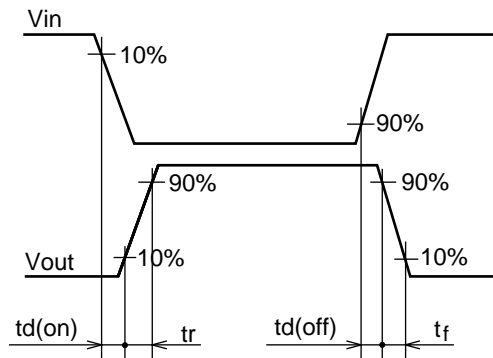


2SJ506(L), 2SJ506(S)

Switching Time Test Circuit

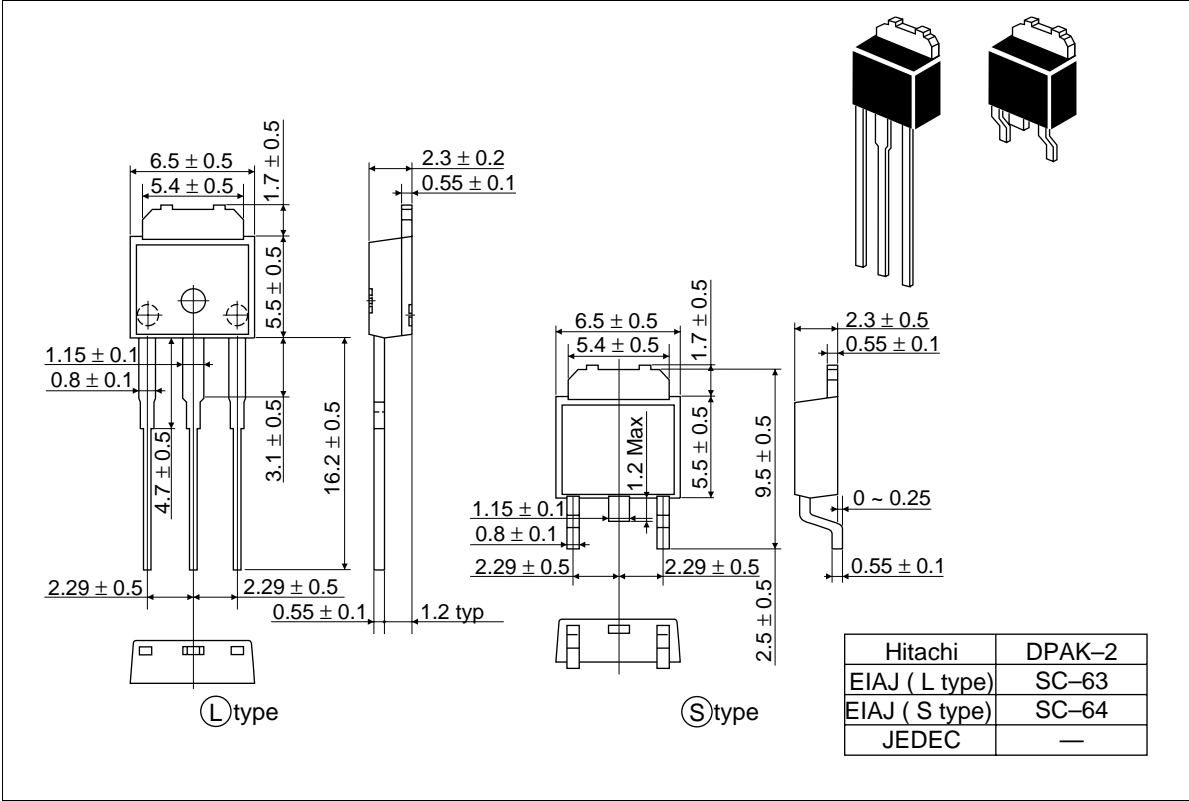


Waveforms



Package Dimensions

Unit: mm



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